

# SS52A THRU SS510A

## SURFACE MOUNT SCHOTTKY BARRIER RECTIFIER

Reverse Voltage - 20 to 100 V

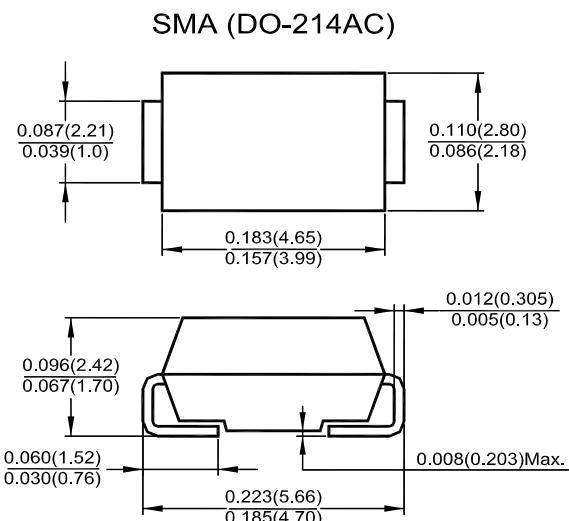
Forward Current - 5 A

### Features

- Metal-semiconductor junction with guard ring
- Epitaxial construction
- Low forward voltage drop
- High current capability
- The plastic material carries UL recognition 94V-0
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

### Mechanical Data

- **Case:** molded plastic
- **Polarity:** Color band denotes cathode



Dimensions in inches and (millimeters)

### Maximum Ratings and Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

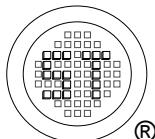
Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20 %.

Parameter	Symbol	SS52A	SS5205A	SS54A	SS55A	SS56A	SS58A	SS510A	Unit
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	20	25	40	50	60	80	100	V
Maximum RMS Voltage	V <sub>RMS</sub>	14	20	28	35	42	56	70	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	20	30	40	50	60	80	100	V
Maximum Average Forward Rectified Current 0.375" (9.5 mm) Lead Lengths at T <sub>L</sub> = 95 °C	I <sub>F(AV)</sub>						5		A
Peak Forward Surge Current 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method)	I <sub>FSM</sub>						150		A
Maximum Forward Voltage at 3 A DC	V <sub>F</sub>	0.38	0.39	0.51	0.6	0.72			V
Maximum DC Reverse Current T <sub>j</sub> = 25 °C at Rated DC Blocking Voltage T <sub>j</sub> = 100 °C	I <sub>R</sub>				0.5	50			mA
Typical Junction Capacitance <sup>1)</sup>	C <sub>j</sub>		500			350			pF
Typical Thermal Resistance <sup>2)</sup>	R <sub>θJA</sub>		15			10			°C/W
Operating Temperature Range	T <sub>j</sub>			- 55 to + 150					°C
Storage Temperature Range	T <sub>stg</sub>			- 55 to + 150					°C

<sup>1)</sup> Measured at 1 MHz and applied reverse voltage of 4 V DC.

<sup>2)</sup> Thermal resistance junction to ambient.



**SEMTECH ELECTRONICS LTD.**



# SS52A THRU SS510A

FIG. 1 – FORWARD CURRENT DERATING CURVE

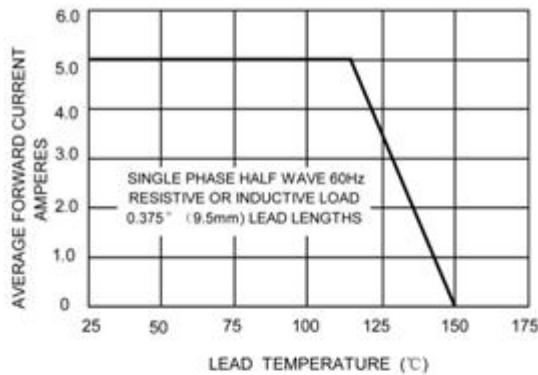


FIG. 2 – MAXIMUM NON-REPETITIVE SURGE CURRENT

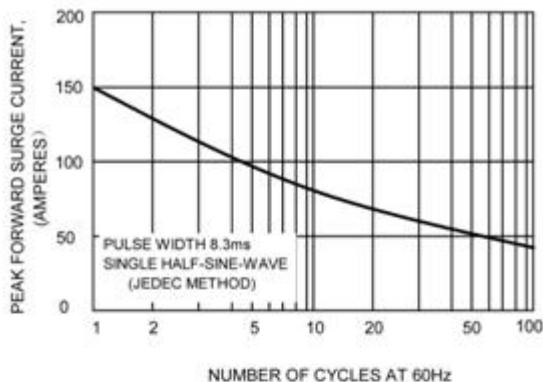


FIG.3 – TYPICAL JUNCTION CAPACITANCE

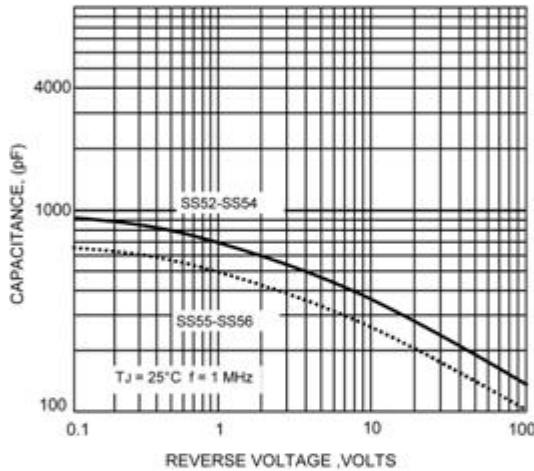


FIG.4-TYPICAL FORWARD CHARACTERISTICS

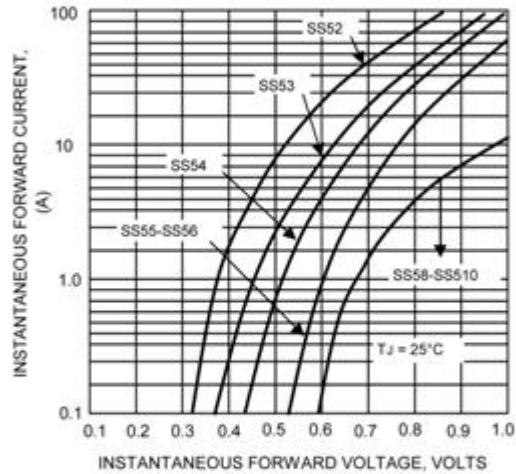
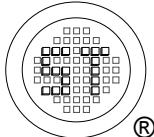
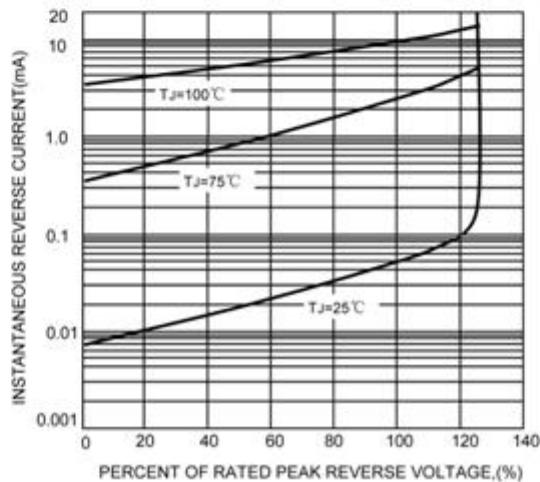


FIG.2-TYPICAL REVER CHARACTERISTICS



SEMTECH ELECTRONICS LTD.



Dated: 24/07/2015 T Rev: 02